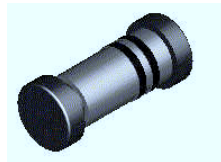
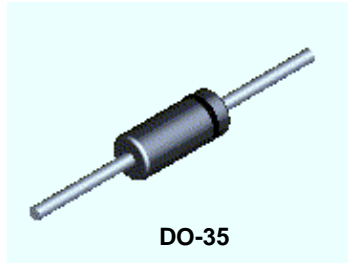


FDH/FDLL 400 / 444



THE PLACEMENT OF THE EXPANSION GAP
HAS NO RELATIONSHIP TO THE LOCATION
OF THE CATHODE TERMINAL

COLOR BAND MARKING		
DEVICE	1ST BAND	2ND BAND
FDLL400	BROWN	VIOLET
FDLL444	BROWN	GRAY

High Voltage General Purpose Diode

Sourced from Process 1J.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
W _{IV}	Working Inverse Voltage	FDH/FDLL 400	150	V
		FDH/FDLL 444	100	V
I _O	Average Rectified Current	200	mA	
I _F	DC Forward Current	500	mA	
i _f	Recurrent Peak Forward Current	600	mA	
i _{f(surge)}	Peak Forward Surge Current	Pulse width = 1.0 second	1.0	A
		Pulse width = 1.0 microsecond	4.0	A
T _{stg}	Storage Temperature Range	-65 to +200	°C	
T _J	Operating Junction Temperature	175	°C	

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 200 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		FDH/FDLL 400 / 444	
P _D	Total Device Dissipation Derate above 25°C	500	mW
		3.33	mW/°C
R _{θJA}	Thermal Resistance, Junction to Ambient	300	°C/W

High Voltage General Purpose Diode

(continued)

Electrical Characteristics

T_A = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
B _V	Breakdown Voltage	FDH/FDLL444	I _R = 100 μA	150	V
		FDH/FDLL400	I _R = 100 μA	200	V
I _R	Reverse Current	FDH/FDLL444	V _R = 100 V		50 nA
			V _R = 100 V, T _A = 150°C		100 μA
		FDH/FDLL400	V _R = 150 V		100 nA
			V _R = 150 V, T _A = 150°C		100 μA
V _F	Forward Voltage	FDH/FDLL444	I _F = 200 mA		1.1 V
			I _F = 300 mA		1.2 V
		FDH/FDLL400	I _F = 200 mA		1.0 V
			I _F = 300 mA		1.1 V
C _O	Diode Capacitance	FDH/FDLL444	V _R = 0, f = 1.0 MHz		2.5 pF
		FDH/FDLL400			2.0 pF
T _{RR}	Reverse Recovery Time	FDH/FDLL444	I _F = I _R = 30 mA, I _{rr} = 3.0 mA, R _L = 100 Ω		60 nS
		FDH/FDLL400	I _F = I _R = 30 mA, I _{rr} = 3.0 mA, R _L = 100 Ω		50 nS

FDH400 / FDLL400 / FDH444 / FDLL444

National Semiconductor was acquired by Texas Instruments.

http://www.ti.com/corp/docs/investor_relations/pr_09_23_2011_national_semiconductor.html

This file is the datasheet for the following electronic components:

FDLL444 - <http://www.ti.com/product/fdll444?HQS=TI-null-null-dscatalog-df-pf-null-wwe>

FDH444 - <http://www.ti.com/product/fdh444?HQS=TI-null-null-dscatalog-df-pf-null-wwe>

FDLL400 - <http://www.ti.com/product/fdll400?HQS=TI-null-null-dscatalog-df-pf-null-wwe>

FDH400 - <http://www.ti.com/product/fdh400?HQS=TI-null-null-dscatalog-df-pf-null-wwe>



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